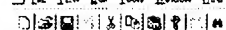


L Number	Hits	Search Text	DB	Time stamp
1	141	((ROM (read adj only)) and (complement\$3 adj3 (bitline digitline (bit adj line) (digit adj line))) and (source near5 connected near5 ground))	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/07/29 18:21
2	14	((ROM (read adj only)) and (complement\$3 adj3 (bitline digitline (bit adj line) (digit adj line))) and (source near5 connected near5 ground)) and (2T 2-T)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/07/29 18:15
3	0	((ROM (read near3 only near3 memory)) same (complement\$3 adj3 (bitline digitline (bit adj line) (digit adj line)))) same (source near5 connected near5 ground)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/07/29 18:22
4	0	((ROM (read near3 only near3 memory)) same (complement\$3 adj3 (bitline digitline (bit adj line) (digit adj line)))) same (source near5 connect\$3 near5 ground)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/07/29 18:23
5	19	((ROM (read near3 only near3 memory)) same (complement\$3 adj3 (bitline digitline (bit adj line) (digit adj line)))) and (source near5 connect\$3 near5 ground)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/07/29 18:34
8	10	((ROM (read near3 only near3 memory)) and (2T (2-T)) and (drain near4 (bitline digitline (bit adj line) (digit adj line))) and (source near4 ground))	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/07/29 18:38
-	500	complement\$3 near3 (bitline digit-line digitline bit-line)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/19 15:08
-	3	((first near3 drain) and (second near3 drain)) same (complement\$3 near3 (bitline digit-line digitline bit-line))	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/08 15:09
-	157	((complement\$3 near3 (bitline digit-line digitline bit-line)) and (true near3 (bitline digit-line digitline bit-line)))	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/11 17:06
-	0	((first near3 drain) and (second near3 drain)) same (complement\$3 near3 (bitline digit-line digitline bit-line)) and ((complement\$3 near3 (bitline digit-line digitline bit-line)) and (true near3 (bitline digit-line digitline bit-line)))	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/08 15:09
-	20030	((first near3 drain) and (second near3 drain))	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/08 15:11
-	183	true near3 (bitline digit-line digitline bit-line)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/08 15:12
-	47	true with complementary with (bitline digitline bit-line digit-line)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/08 15:13

5	((first near3 drain) and (second near3 drain)) and (true with complementary with (bitline digitline bit-line digit-line))	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/08 15:13
9984	2T 2-transistor two-transistor	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/19 15:12
2	((2T 2-transistor two-transistor) and (complement\$3 near3 (bitline digit-line digitline bit-line))) and ((complement\$3 near3 (bitline digit-line digitline bit-line)) and (true near3 (bitline digit-line digitline bit-line)))	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/11 17:06
215	(true with complement\$3) same (bitline digit-line digitline bit-line)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/19 15:10
16	((true with complement\$3) same (bitline digit-line digitline bit-line)) and (first near3 drain) and (second near3 drain)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/19 15:17
21563	float\$3 near3 source) (insulat\$3 near3 source	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/19 15:22
14	((true with complement\$3) same (bitline digit-line digitline bit-line)) and (float\$3 near3 source) (insulat\$3 near3 source)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/19 15:22
21563	float\$3 near3 source) (insulat\$3 near3 source	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/19 15:23
2	((true with complement\$3) same (bitline digit-line digitline bit-line)) and (float\$3 near3 source) (insulat\$3 near3 source)) and (source near4 connect\$3 near4 ground)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/21 11:37
10	(2T 2-transistor two-transistor) and (complement\$3 near3 (bitline digit-line digitline bit-line))	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/19 15:24
205	(true and complement\$2) same (bitline bit-line (bit adj2 line)) and (drain same source same ground)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/21 12:10
148	(true and complement\$2) same (bitline bit-line (bit adj2 line)) and (drain with source with ground)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/21 11:44
0	((true and complement\$2) same (bitline bit-line (bit adj2 line)) and (drain with source with ground)) and (2T)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/21 11:44
0	((true and complement\$2) same (bitline bit-line (bit adj2 line)) and (drain same source same ground)) and (2T)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/21 11:45

-	91	((true and complement\$2) same (bitline bit-line (bit adj2 line)) and (drain with source with ground)) and complementary	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/21 11:45
-	127	((true and complement\$2) same (bitline bit-line (bit adj2 line)) and (drain same source same ground)) and complementary	USPÄT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/21 11:46
-	96	((true and complement\$2) same (bitline bit-line (bit adj2 line)) and (drain same source same ground)) and ((read adj2 only) ROM)	USPÄT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/21 12:11
-	93	((true and complement\$2) same (bitline bit-line (bit adj2 line)) and (drain same source same ground)) and ((read adj only) ROM)	USPÄT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/21 12:11
-	51	((true and complement\$2) same (bitline bit-line (bit adj2 line)) and (drain same source same ground)) and (ROM)	USPÄT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/03/21 12:11



- ☐ Drafts  
☐ Pending  
☒ Archived  
☐ L1 (141) (ROM (read adj only)) and (complement\$3 adj3 (bitline digitline (bit  
☐ L2 (14) L1 and (2T 2 T)  
☐ L3 (0) (ROM (read near3 only near3 memory)) same (complement\$3 adj3 (bitline  
☐ L4 (0) (ROM (read near3 only near3 memory)) same (complement\$3 adj3 (bitline  
☐ L5 (19) (ROM (read near3 only near3 memory)) same (complement\$3 adj3 (bitline  
☐ L6 (10) (ROM (read near3 only near3 memory)) and (2T (2-T)) and (drain near4 (0  
☐ Failed  
☐ Saved  
☐ Favorites  
☐ Tagged (2)  
☐ UNC  
☐ Queue  
☐ Trash

QDC: USPAT.US#SPUB.EPO.JPO.DERWENT.BM.TDB

Details operator: CR

☐ Back  
☒ Highlight all terms ready

(0) M (read near3 only near3 memory) and (2T (2-T)) and (drain near4 (0) and (bitline digitline (bit AD line) digit AD line) and (drain near4 (0)

U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	Inventor	S	C	P	U	W	A
1	<input type="checkbox"/>	US 20020031216 A1	20020103	24	DISCRETE DEVICES INCLUDING BAPROM TRANSISTOR AND NVRAM	365/145	257 E27.104		FORBES, LEONARD et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	US 20010051224 A1	20011227	24	Semiconductor memory device and testing system and	365/200			Koike, Hiroki	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	US 6610072 B1	20030121	7	TWO transistor ferroelectric non volatile memory	365/145	257 295; 365/145		Lee, Jong-Jan et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
4	<input type="checkbox"/>	US 633/805 B1	20020118	26	Discrete devices including BAPROM transistor and NVRAM	365/145	257 E27.104; 365/145		Forbes, Leonard et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
5	<input type="checkbox"/>	US 6151242 A	20011121	147	Semiconductor memory device	365/145	365/145; 365/230.03		Takachima, Daisaku	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
6	<input type="checkbox"/>	US 6391622 A	20000718	36	Nonvolatile ferroelectric memory device	365/145	365/145; 365/230.06		Kang, Hee Bok	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
7	<input type="checkbox"/>	US 5701469 A	19980714	07	Semiconductor memory device comprising two kinds of	365/149	365/154; 365/185.08;		Matsuo, Ryuichi et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

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